

Claims

1 A high frequency semiconductor device having a shifted doping profile,
2 comprising:

3 a buried oxide layer formed over a semiconductor substrate; and
4 a silicon layer formed over the buried oxide layer, wherein an origin of a
5 doping profile of the silicon layer is within a body region of the device.

6 2. The device of claim 1, wherein the silicon layer comprises a source region, a
7 body region, a drain region, and a drift region,

8 3. The device of claim 1, further comprising a top oxide layer, wherein the origin
9 of the doping profile is offset approximately 2 to 4 μ m from an edge of the top
10 oxide layer.

11 4. The device of claim 1, further comprising a field plate formed over the top
12 oxide layer and a plate oxide layer formed over the field plate.

13 5. The device of claim 4, further comprising a source metal, a gate metal, and a
14 drain metal formed over the silicon layer.

15 6. The device of claim 1, wherein the doping profile is linear.

1 7. The device of claim 1, wherein the doping profile is non-linear.

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8. A high frequency semiconductor device having a shifted doping profile,

comprising:

a buried oxide layer formed over a semiconductor substrate;

a silicon layer formed over the buried oxide layer, wherein the silicon layer comprises a source region, a body region, a drift region, and a drain region;

and

a top oxide layer formed over the silicon layer, wherein a doping profile of the silicon layer has an origin within the body region, approximately 2 to 4 μ m from an edge of the top oxide layer.

9. The device of claim 8, wherein the doping profile is linear.

10. The device of claim 8, wherein the doping profile is non-linear.

11. The device of claim 8, further comprising a field plate formed over the top oxide layer and a plate oxide layer formed over the field plate.

12. The device of claim 11, further comprising a source metal, a gate metal, a drain metal formed over the silicon layer.

1 13. The device of claim 8, wherein the device has a transconductance
2 approximately 15% higher and a maximum current approximately 45 % higher
3 than a device having a doping profile origin approximately aligned with the edge
4 of the top oxide layer.

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18. The method of claim 14, wherein the doping profile is linear.

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19. The method of claim 14, wherein the doping profile is non-linear.

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20. The method of claim 14, further comprising:

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forming a field plate over the top oxide layer;

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forming a plate oxide over the field plate; and

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forming a source metal, a gate metal, and a drain metal over the silicon

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layer.